

# FABRICATION OF LARGE SCALE $PbZr_xTi_{1-x}O_3$ (PZT) THIN FILMS BY OFF-AXIS PULSED LASER DEPOSITION (PLD) TECHNIQUE

**IITM Technology Available for Licensing**

## Problem Statement

- PZT is desirable for fabricating electrical devices like power harvesters, sensors, surface acoustic wave devices etc. due to its favorable electrical properties
- PZT in thin film form exhibits lower leakage current density, higher remanent polarization for fast polarization switching, and can sustain high dielectric strength compared to bulk polycrystalline ceramics.
- Developing PZT thin films over large areas is challenging due to the volatile nature of Pb at high processing temperatures and the need to maintain stoichiometry across the entire deposited area.

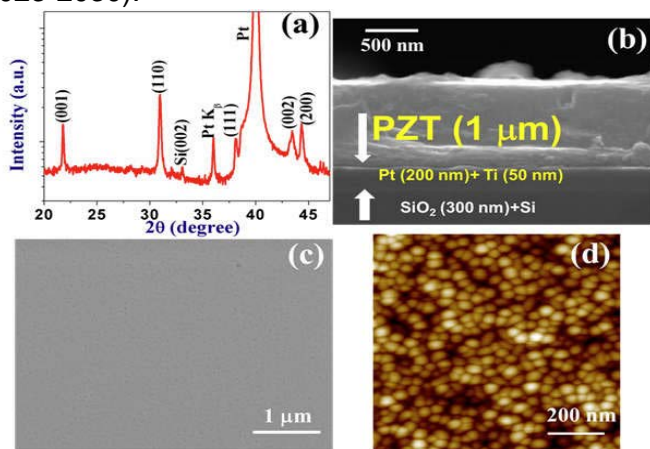
## Technology Category/ Market

**Category – Advanced materials**

**Applications** –Sensors, Semiconductors, acoustic devices, power harvesting systems

**Industry** – Electrical, Manufacturing

**Market** -Piezoelectric Materials Market size was valued at USD 29.23 billion in 2021 and is poised to grow from USD 30.9 billion in 2022 to USD 48.14 billion by 2030, growing at a CAGR of 5.7% in the forecast period (2023-2030).



**Fig.1** (a) shows XRD pattern of the PZT (48/52) thin film on Pt/TiO<sub>2</sub>/SiO<sub>2</sub>/Si substrate, (b) Cross-sectional SEM images of the PLD grown PZT thin films coated on Pt/TiO<sub>2</sub>/SiO<sub>2</sub>/Si substrate (c) SEM image and (d) AFM topography image of the large area thin films

## Technology

The present invention discloses a method involves the fabrication of high-quality large-scale  $PbZr_xTi_{1-x}O_3$ (PZT) thin films on a platinum-coated silicon substrate.

**Composition and Preparation:** PZT thin films are prepared from stoichiometric quantities of the oxide powders PbO, ZrO<sub>2</sub>, and TiO<sub>2</sub> through a solid-state reaction route

### Raster Mechanism:

A programmable raster mirror is utilized and positioned above the quartz window for precision and deposition

### Laser Beam Scanning:

The programmable rastered laser beam is fixed with a scan rate of 300 steps/sec

### Scanning Pattern:

•starts from the edge of the target, moves towards the center of the 2-inch rotating PZT target, and then reverses its direction.

**Incidence Angle:** The laser beam is directed onto the target with a specific incidence angle of 45 degrees.

### Chamber Conditions and Annealing:

Partial pressure of 0.3 mbar of oxygen (O<sub>2</sub>) is maintained inside the chamber, followed by deposition, and 60-minute post-deposition annealing to form PZT thin films

## Research Lab

**Prof. RAMACHANDRA RAO M S**

**Prof. SETHUPATHI K**

Dept. of Physics

## CONTACT US

**Dr. Dara Ajay, Head**

Technology Transfer Office,  
IPM Cell- IC&SR, IIT Madras

**IITM TTO Website:**

<https://ipm.icsr.in/ipm/>

**Email:** [smipm-icsr@icsrpis.iitm.ac.in](mailto:smipm-icsr@icsrpis.iitm.ac.in)

[sm-marketing@imail.iitm.ac.in](mailto:sm-marketing@imail.iitm.ac.in)

**Phone:** +91-44-2257 9756/ 9719

**Industrial Consultancy & Sponsored Research (IC&SR)**

**Key Features / Value Proposition**

**Technical Perspective**

- ❑ The invention relates to ferroelectric large area PZT thin films, grown on oriented Pt coated Si substrate using off-axis pulsed laser deposition (PLD) with a beam rastering mechanism.
- ❑ This method combines specific deposition conditions, scanning patterns, and post-treatment processes to produce large-scale, high-quality PZT thin films

**User Perspective**

- ❑ Large area PZT thin films are used in underwater SONAR devices, power harvester, sensors, acoustic devices, MEMS etc
- ❑ The interface between the as-grown large PZT thin films and the Pt coated Si substrate is well defined, flat and sharp

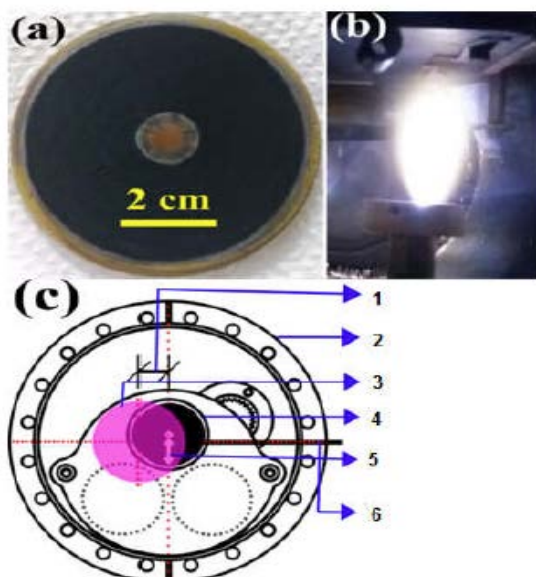
**Intellectual Property**

- IITM IDF Ref. 1574
- IN 458560-Granted

**TRL (Technology Readiness Level)**

**TRL- 3, Experimental proof of concept**

**Images**



**Fig. 2** (a) picture of two inch PZT target after laser ablation (b) an actual photograph of the plume during rasting mechanism (c) schematic representation of the rasting mechanism for growth of large area PZT thin films with levelling , 1) off-axis about 19mm between the center of the rotating substrate and the centre of the ablated target, 2) outerdiameter of the chamber, 3) 3 inch substrate holder, 4) 2 inch target holder, 5) rasting direction from the edge of the rotating target to the centre and then backward and 6) laser direction i.e.the laser falls on the target with an incidence angle of 450.

**CONTACT US**

**Dr. Dara Ajay, Head**  
Technology Transfer Office,  
IPM Cell- IC&SR, IIT Madras

**IITM TTO Website:**  
<https://ipm.icsr.in/ipm/>

**Email:** [smipm-icsr@icsrpis.iitm.ac.in](mailto:smipm-icsr@icsrpis.iitm.ac.in)

[sm-marketing@imail.iitm.ac.in](mailto:sm-marketing@imail.iitm.ac.in)

**Phone:** +91-44-2257 9756/ 9719